

Vishay Semiconductors

Ultrafast Rectifier, 2 x 10 A FRED Pt®



| PRODUCT SUMMARY | | | | | |
|----------------------------------|----------------------|--|--|--|--|
| Package | TO-220AB | | | | |
| I _{F(AV)} | 2 x 10 A | | | | |
| V_{R} | 200 V | | | | |
| V _F at I _F | See Electrical table | | | | |
| t _{rr} typ. | See Recovery table | | | | |
| T _J max. | 175 °C | | | | |
| Diode variation | Common cathode | | | | |

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature



- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





ROHS

DESCRIPTION/APPLICATIONS

VS-MUR2020CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | |
|---|--------------|-----------------------------------|---|----------------|-------|--|--|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MAX. | UNITS | | |
| Peak repetitive reverse voltage | | V_{RRM} | | 200 | V | | |
| Average rectified forward current | per leg | I | | 10 | | | |
| | total device | I _{F(AV)} | Rated V _R , T _C = 145 °C | 20 | Α | | |
| Non-repetitive peak surge current per leg | | I _{FSM} | | 100 | A | | |
| Peak repetitive forward current per leg | | I _{FM} | Rated V _R , square wave, 20 kHz, T _C = 145 °C | 20 | | | |
| Operating junction and storage temperatures | | T _J , T _{Stg} | | - 65 to 175 | °C | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|-------------------------------------|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | Ι _R = 100 μΑ | 200 | - | - | |
| Forward voltage | | I _F = 8 A, T _J = 125 °C | - | - | 0.85 | V |
| | V _F | I _F = 16 A | - | - | 1.15 | |
| | | I _F = 16 A, T _J = 125 °C | - | - | 1.05 | |
| Deverse leekees europt | | $V_R = V_R$ rated | - | - | 15 | |
| Reverse leakage current I _R | | T _J = 150 °C, V _R = V _R rated | - | - | 250 | μΑ |
| Junction capacitance | C _T | V _R = 200 V | - | 55 | - | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH |

VS-MUR2020CTPbF

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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|---|-----------------|--|---|-------|------|-------|-----|--|
| PARAMETER | SYMBOL | TEST CO | MIN. | TYP. | MAX. | UNITS | | |
| Reverse recovery time | | $I_F = 1.0 A, dI_F/dt =$ | 50 A/μs, V _R = 30 V | - | - | 35 | | |
| | | I _F = 0.5 A, I _R = 1.0 | A, I _{REC} = 0.25 A | | - | 25 | | |
| | t _{rr} | T _J = 25 °C | | - | 21 | - | ns | |
| | | T _J = 125 °C | | - | 35 | - | | |
| Peak recovery current | | T _J = 25 °C | I _F = 10 A dI _F /dt = 200 A/μs | - | 1.9 | - | Α | |
| | IRRM | T _J = 125 °C | V _R = 160 V | - 4.8 | 4.8 | - | ^ | |
| Reverse recovery charge | 0 | T _J = 25 °C | , , , , , , , , , , , , , , , , , , , | - 25 | 25 | - | nC | |
| | Q _{rr} | T _J = 125 °C | | - | 78 | - | IIC | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|---|-----------------------------------|--|-----------|------|------|------------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | - 65 | - | 175 | °C | |
| Thermal resistance, per leg | D | | - | - | 2.5 | | |
| junction to case total device | R_{thJC} | | - | - | 1.25 | | |
| Thermal resistance, junction to ambient per leg | R _{thJA} | | - | - | 50 | °C/W | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | | |
| Woight | | | - | 2.0 | - | g | |
| Weight | | | - | 0.07 | - | oz. | |
| Mounting torque | | | 6.0 | _ | 12 | kgf · cm | |
| Wounting torque | | | (5.0) | | (10) | (lbf · in) | |
| Marking device | | Case style TO-220AB | MUR2020CT | | | | |



Ultrafast Rectifier, 2 x 10 A FRED Pt® Vishay Semiconductors

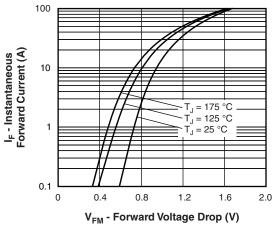


Fig. 1 - Maximum Forward Voltage Drop Characteristics

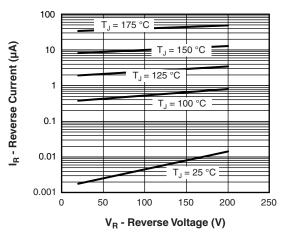


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

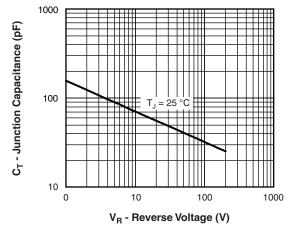


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

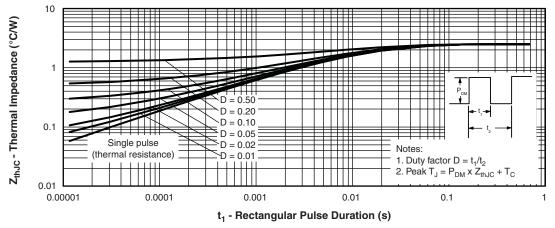


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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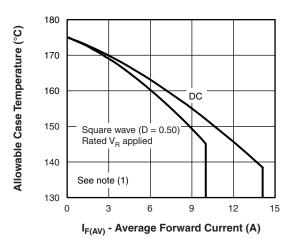


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

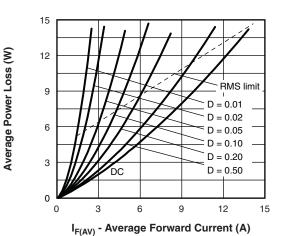


Fig. 6 - Forward Power Loss Characteristics

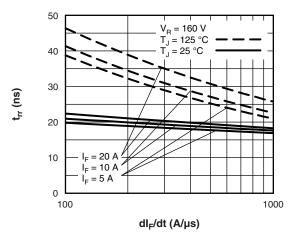


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

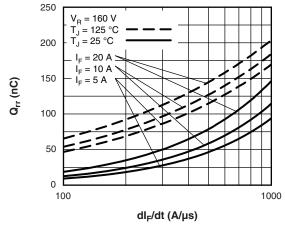


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$



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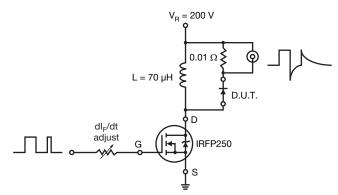
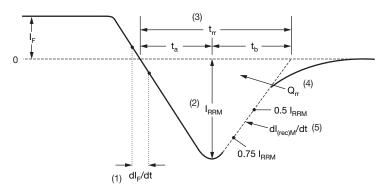


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

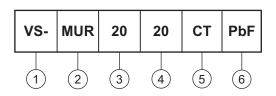
Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Ultrafast Rectifier, 2 x 10 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (20 = 20 A)

4 - Voltage rating (20 = 200 V)

5 - CT = Center tap (dual)

6 - PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

| LINKS TO RELATED DOCUMENTS | | | | | |
|----------------------------|--------------------------|--|--|--|--|
| Dimensions | www.vishay.com/doc?95222 | | | | |
| Part marking information | www.vishay.com/doc?95225 | | | | |
| SPICE model | www.vishay.com/doc?95272 | | | | |



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

| SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|--------|--------|--------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.25 | 4.65 | 0.167 | 0.183 | |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | |
| A2 | 2.56 | 2.92 | 0.101 | 0.115 | |
| b | 0.69 | 1.01 | 0.027 | 0.040 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 |
| D | 14.85 | 15.25 | 0.585 | 0.600 | 3 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | |
| D2 | 11.68 | 12.88 | 0.460 | 0.507 | 6 |

| SYMBOL | MILLIM | IETERS | INC | HES | NOTES |
|---------|--------|--------|------------|-------|-------|
| STIMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| E | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| E2 | - | 0.76 | - | 0.030 | 7 |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6, 7 |
| L | 13.52 | 14.02 | 0.532 | 0.552 | |
| L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| ØΡ | 3.54 | 3.73 | 0.139 | 0.147 | |
| Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| θ | 90° t | o 93° | 90° to 93° | | |
| | | • | • | • | |

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip





Vishay

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